

SAMYANG ELECTRONICS MBR1535CT --- MBR15200CT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- \bigotimes Low forward voltage drop,low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- \bigcirc The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- - MIL-STD-750,Method 2026
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

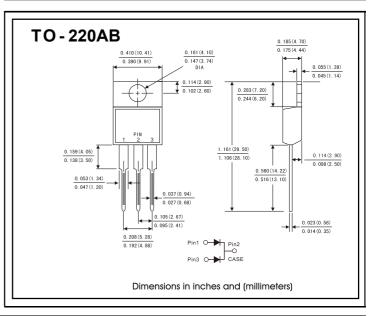
		Symbols	MBR 1535CT	MBR 1545CT	MBR 1550CT	MBR 1560CT	MBR 15100CT	MBR 15150CT	MBR 15200CT	Units
Maximum repetitive peak reverse voltage		Vrrm	35	45	50	60	100	150	200	Volts
Maximum RMS voltage		Vrms	25	32	35	42	70	105	140	Volts
Maximum DC blocking voltage		Vdc	35	45	50	60	100	150	200	Volts
Maximum average forward rectified current(see Fig.1) T	Per leg otal device	l(AV)	15.0						Amps	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		FSM	150.0							Amps
Maximum instantaneous forward voltage at 15 A		VF	0.60		().75	0.85	0. 90	0. 95	Volts
Maximum instantaneous reverse	T _c =25℃		0.2							
current at rated DC blocking voltage(Note 1)	$T_c = 125^{\circ}C$	R	30			50				mA
Typical thermal resistance (Note 2)		R_{θ} JC	3.0							°C/W
Operating junction temperature range		TJ	-65 to+150							°C
Storage temperature range		Tstg	-65 to+150							ĉ

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

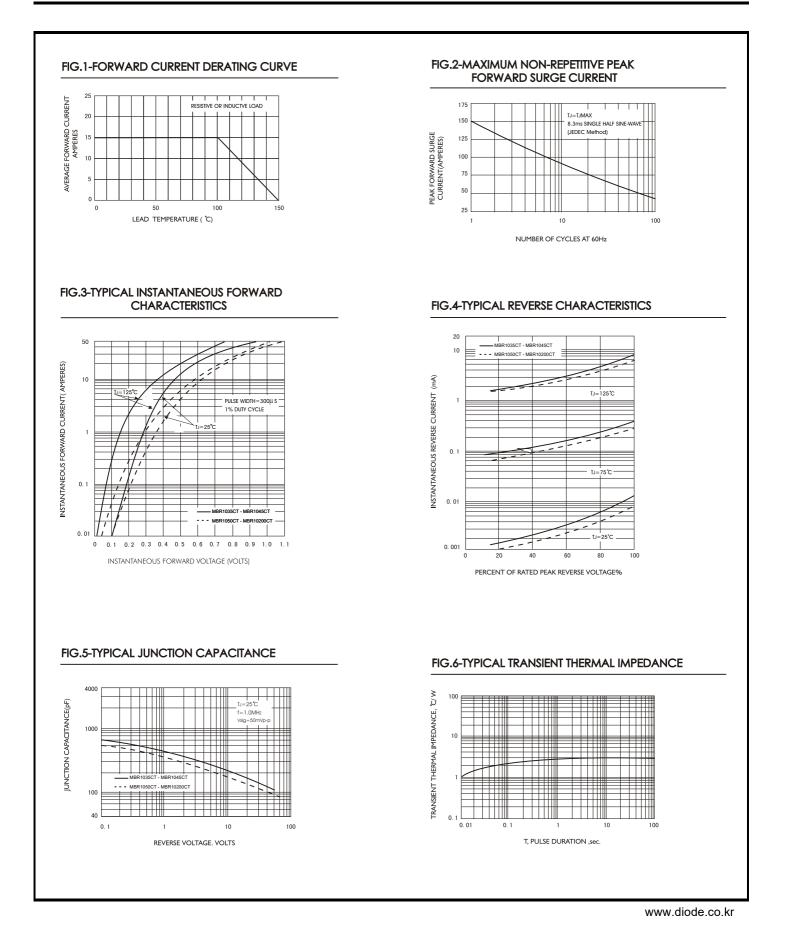
3. Thermal resistance junction to ambient

VOLTAGE RANGE: 35 --- 200 V CURRENT:15.0A



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RATINGS AND CHARACTERISTIC CURVES



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